

Method for Fabricating Silicide

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Abstract

A processing method for fabricating silicide is provided. First of all, a semiconductor structure having a semiconductor surface and an insulation surface is provided. Next, an epitaxial layer on the semiconductor surface is formed. And, the semiconductor structure is treated. The treat step is that the removal rate of the insulation surface is faster than the removal rate of the epitaxial layer. Then, a metal layer on the epitaxial layer is formed. Finally, heating the epitaxial layer forms silicide. The treatment step prevents the insulation surface from the formation of the silicide so as to reduce the degradation of device characteristics.